



S/N 07/964,362

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Sang Young KIM, et al. Examiner: B. Everhart
Serial No.: 07/964,362 Group Art Unit: 1109
Filed: 10/21/92 Docket: 9983.3US01
Title: METHOD FOR FILLING CONTACT HOLES WITH METAL BY
TWO-STEP DEPOSITION

AMENDMENT

Hon. Commissioner of Patents
and Trademarks
Washington, D.C. 20231

Sir:

In response to the Office Action mailed October 21,
1993, regarding the above-identified patent application,
Applicants respectfully request the following amendments be made.

IN THE CLAIMS

Amend the claims as follows:

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2. (Once Amended) The methods of claim 1, wherein the [first
contact hole and the second contact hole are filled with the]
first metal layer and subsequently the second metal layer [of
selective tungsten layer, respectively,] are formed by chemical
vapor deposition method.

Add the following new claims: